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(54) Title: VFET CONTACT FORMATION

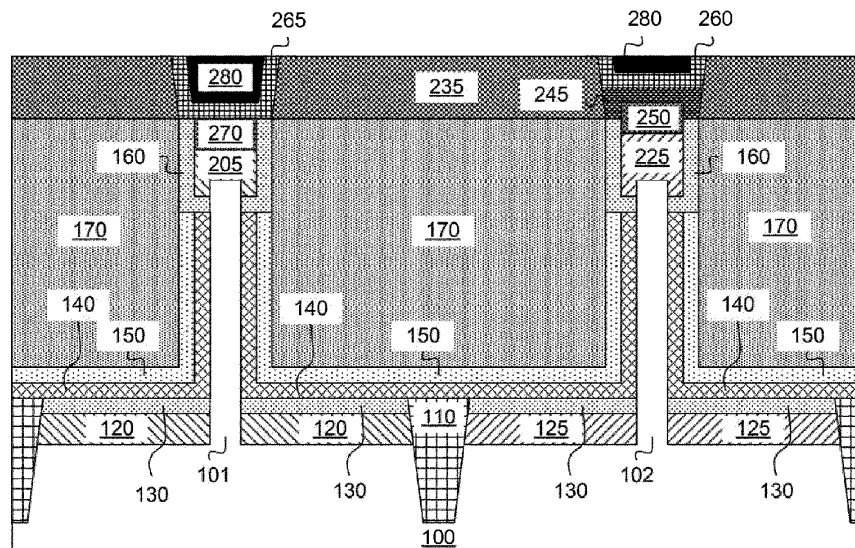


FIG. 14

(57) Abstract: An embodiment of the invention may include a Vertical Field Effect Transistor (VFET) structure, and method of making that structure, having a first VFET and a second VFET. The first VFET may include a single liner (260) between a first source/drain epi (200) and a contact (280). The second VFET may include two liners (260) between a second source/drain epi (225) and a contact (280). This may enable proper contact liner matching for differing VFET devices.

[Continued on next page]

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